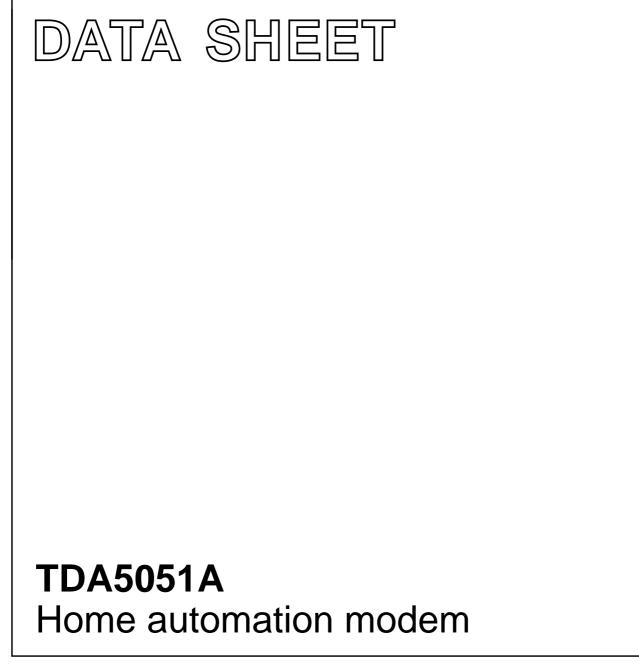
# INTEGRATED CIRCUITS



Product specification File under Integrated Circuits, IC11 1997 Sep 19



HILIP

# TDA5051A

### FEATURES

- · Full digital carrier generation and shaping
- Modulation/demodulation frequency set by clock adjustment, from microcontroller or on-chip oscillator
- High clock rate of 6 bits D/A (Digital to Analog) converter for rejection of aliasing components
- Fully integrated output power stage with overload protection
- Automatic gain control at receiver input
- 8-bit A/D and narrow digital filtering
- Digital demodulation delivering baseband data
- Easy compliance with EN50065-1 with simple coupling network
- Few external components for low cost applications
- SO16 plastic package.

# APPLICATIONS

- Home appliance control (air conditioning, shutters, lighting, alarms and so on)
- Energy/heating control
- ASK (Amplitude Shift Keying) data transmission using the home power network.

### **GENERAL DESCRIPTION**

The TDA5051A is a modem IC, specifically dedicated to ASK transmission by means of the home power supply network, at 600 or 1200 baud data rate. It operates from a single 5 V supply.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>DD</sub>	supply voltage		4.75	5.0	5.25	V
I <sub>DD(tot)</sub>	total supply current	f <sub>osc</sub> = 8.48 MHz				
	reception mode		-	28	38	mA
	transmission mode ( $\overline{DATA}_{IN} = 0$ )	$Z_L = 30 \Omega$	-	47	68	mA
	power down mode		-	19	25	mA
T <sub>amb</sub>	operating ambient temperature		0	-	70	°C
f <sub>cr</sub>	carrier frequency	note 1	95	132.5	148.5	kHz
f <sub>osc</sub>	oscillator frequency		6.08	8.48	9.504	MHz
V <sub>o(rms)</sub>	output carrier signal on CISPR16 load (RMS value)		120	-	122	dBμV
V <sub>i(rms)</sub>	input signal (RMS value)	note 2	82	_	122	dBµV
THD	total harmonic distortion on CISPR16 load with coupling network		-	-55	-	dB
ZL	load impedance		1	30	-	Ω
BR	baud rate		-	600	1200	bits/s

### Notes

- 1. Frequency range corresponding to the EN50065-1 band. However the modem can operate at any lower oscillator frequency.
- 2. The minimum value can be improved by using an external amplifier (see application diagrams, Figs 22 and 23).

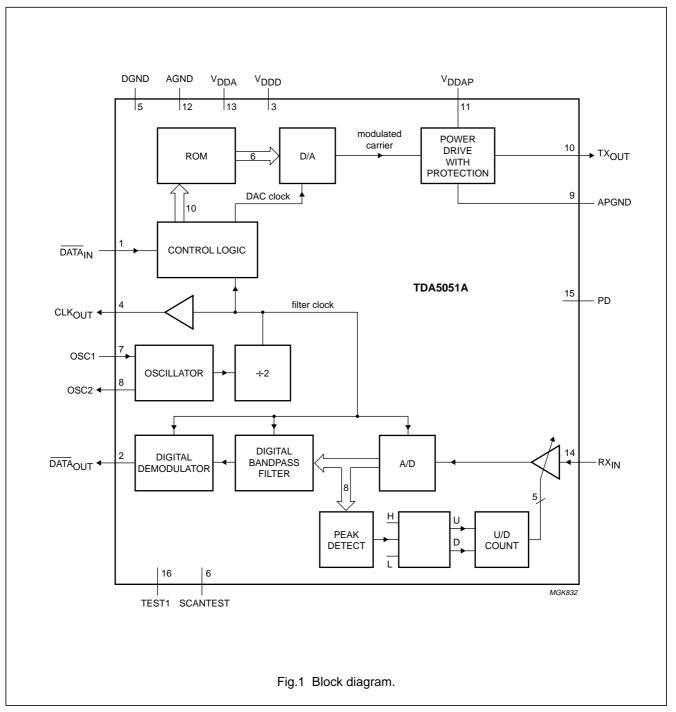
### QUICK REFERENCE DATA

TDA5051A

### ORDERING INFORMATION

TYPE		PACKAGE			
NUMBER	NAME	ME DESCRIPTION VERSI			
TDA5051AT	SO16	plastic small outline package: 16 leads; body width 7.5 mm	SOT162-1		

### **BLOCK DIAGRAM**



# TDA5051A

### PINNING

SYMBOL	PIN	DESCRIPTION				
DATA <sub>IN</sub>	1	digital data input (active LOW)				
DATA <sub>OUT</sub>	2	digital data output (active LOW)				
V <sub>DDD</sub>	3	digital supply voltage	DATA <sub>IN</sub> 1	DATA <sub>IN</sub> 1	DATA <sub>IN</sub> 1	DATA <sub>IN</sub> 1 16 TEST1
CLK <sub>OUT</sub>	4	clock output	DATA <sub>OUT</sub> 2	DATA <sub>OUT</sub> 2	DATA <sub>OUT</sub> 2	DATA <sub>OUT</sub> 2 15 PD
DGND	5	digital ground	V <sub>DDD</sub> 3	V <sub>DDD</sub> 3	V <sub>DDD</sub> 3	V <sub>DDD</sub> 3 14 RX <sub>IN</sub>
SCANTEST	6	test input (LOW in application)	CLK <sub>OUT</sub> 4	CLKOUT 4	CLKOUT 4	CLK <sub>OUT</sub> 4
OSC1	7	oscillator input	DGND 5	TDA5	TDA5051AT	
OSC2	8	oscillator output	SCANTEST 6			
APGND	9	analog ground for power amplifier				
TX <sub>OUT</sub>	10	analog signal output	OSC1 7	OSC1 7	OSC1 7	OSC1 7 10 TX <sub>OUT</sub>
V <sub>DDAP</sub>	11	analog supply voltage for power	OSC2 8	OSC2 8	OSC2 8	OSC2 8 9 APGND
	<b> </b>	amplifier			MGK833	MGK833
AGND	12	analog ground				
V <sub>DDA</sub>	13	analog supply voltage				
RX <sub>IN</sub>	14	analog signal input				
PD	15	power-down input (active HIGH)	Fig.2	Fig.2 Pin c	Fig.2 Pin configu	Fig.2 Pin configuration.
TEST1	16	test input (HIGH in application)				

# TDA5051A

### FUNCTIONAL DESCRIPTION

Both transmission and reception stages are controlled either by the master clock of the microcontroller, or by the on-chip reference oscillator connected to a crystal. This holds for the accuracy of the transmission carrier and the exact trimming of the digital filter, thus making the performance totally independent of application disturbances such as component spread, temperature, supply drift and so on.

The interface with the power network is made by means of a LC network (see Fig.18). The device includes a power output stage able to feed a 120 dB $\mu$ V (RMS) signal on a typical 30  $\Omega$  load.

To reduce power consumption, the IC is disabled by a power-down input (pin PD): in this mode, the on-chip oscillator remains active and the clock continues to be supplied at pin CLK<sub>OUT</sub>. For low-power operation in reception mode, this pin can be dynamically controlled by the microcontroller (see Section "Power-down mode").

When the circuit is connected to an external clock generator (see Fig.6), the clock signal must be applied at pin OSC1 (pin 7); OSC2 (pin 8) must be left open. Use of the on-chip clock circuitry is shown in Fig.7.

All logic inputs and outputs are compatible with TTL/CMOS levels, providing an easy connection to a standard microcontroller I/O port.

The digital part of the IC is fully scan-testable. Two digital inputs, SCANTEST and TEST1, are used for production test: these pins must be left open in functional mode (correct levels are internally defined by pull-up/down resistors).

### **Transmission mode**

The carrier frequency is generated by the scanning of a ROM memory under the control of the microcontroller clock or the reference frequency provided by the on-chip oscillator, thus providing strict stability with respect to environmental conditions. High frequency clocking rejects the aliasing components to such an extent that they are filtered by the coupling LC network and do not cause any significant disturbance. The data modulation is applied through pin DATA<sub>IN</sub> and smoothly applied by specific digital circuitry to the carrier (shaping). Harmonic components are limited in this process, thus avoiding unacceptable disturbance of the transmission channel (according to CISPR16 and EN50065-1 recommendations). A -55 dB total harmonic distortion is reached when using the typical LC coupling network (or an equivalent filter).

The D/A converter and the power stage are set in order to provide a maximum signal level of 122 dB $\mu$ V (RMS) at the output.

The output of the power stage  $(TX_{OUT})$  **always** has to be connected to a decoupling capacitor, because of a DC level of  $0.5V_{DD}$  at this pin, present even when the device is not transmitting. This pin also has to be **protected against overvoltage and negative transient signals**. The DC level of  $TX_{OUT}$  can be used to bias an unipolar transient suppressor, as shown in the application diagram (see Fig.18).

Direct connection to the mains is done through a LC network for low-cost applications. However, a HF signal transformer could be used when power-line insulation has to be performed.

### CAUTION

In transmission mode, the receiving part of the circuit is **not disabled** and the detection of the transmitted signal is normally performed. In this mode, the gain chosen before the beginning of the transmission is stored, and the **AGC is internally set to** –6 dB as long as  $DATA_{IN}$  is LOW. Then, the old gain setting is **automatically restored**.

### **Receiving mode**

The input signal received by the modem is applied to a wide range input amplifier with Automatic Gain Control (AGC) (–6 to +30 dB). This is basically for noise performance improvement and signal level adjustment that ensures a maximum sensitivity of the A/D converter. Then an 8-bit A/D conversion is performed, followed by digital bandpass filtering, in order to meet the CISPR normalization and to comply with some additional limitations encountered in current applications. After digital demodulation, the baseband data signal is made available after pulse shaping.

The signal pin (RX<sub>IN</sub>) is a high-impedance input, which has to be protected and DC decoupled for the same reasons as with pin TX<sub>OUT</sub>. The high sensitivity (82 dBµV) of this input requires an efficient 50 Hz rejection filter (realized by the LC coupling network) also used as an anti-aliasing filter for the internal digital processing (see Fig.18).

# TDA5051A

### Data format

TRANSMISSION MODE

The data input  $(\overline{DATA}_{IN})$  is active LOW: this means that a burst is generated on the line (pin TX<sub>OUT</sub>) when pin  $\overline{DATA}_{IN}$  is LOW.

Pin  $TX_{OUT}$  is in high-impedance state as long as the device is not transmitting. Successive logic 1s are treated in a NRZ mode (see pulse shape description in Figs 8 and 9).

### RECEIVING MODE

The data output (pin  $\overline{\text{DATA}}_{\text{OUT}}$ ) is active LOW; this means that the data output is LOW when a burst is received. Pin  $\overline{\text{DATA}}_{\text{OUT}}$  remains LOW as long as a burst is received.

### Power-down mode

Power-down input (pin PD) is active HIGH; this means that the power consumption is minimal when pin PD is HIGH. All functions, except clock generation, are disabled then.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V <sub>DD</sub>	supply voltage	4.5	5.5	V
f <sub>osc</sub>	oscillator frequency	_	12	MHz
T <sub>stg</sub>	storage temperature	-50	+150	°C
T <sub>amb</sub>	operating ambient temperature	-10	+80	°C
Tj	junction temperature	_	125	°C

### HANDLING

Inputs and outputs are protected against electrostatic discharge in normal handling. However, to be totally safe, it is desirable to take normal precautions appropriate to handling MOS devices.

# TDA5051A

### CHARACTERISTICS

 $V_{DDD} = V_{DDA} = 5 \text{ V} \pm 5\%$ ;  $T_{amb} = 0$  to +70 °C;  $V_{DDD}$  connected to  $V_{DDA}$ ; DGND connected to AGND.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	
Supply					ł	
V <sub>DD</sub>	supply voltage		4.75	5	5.25	V
I <sub>DD(RX/TX)(tot)</sub>	total analog + digital supply current; TX or RX mode	V <sub>DD</sub> = 5 V ±5%	-	28	38	mA
I <sub>DD(PD)(tot)</sub>	total analog + digital supply current; power-down mode	V <sub>DD</sub> = 5 V ±5%; PD = HIGH	-	19	25	mA
I <sub>DD(PAMP)</sub>	power amplifier supply current in transmission mode	$V_{DD} = 5 V \pm 5\%;$ $\frac{Z_L = 30 \Omega;}{DATA_{IN}} = LOW$	-	19	30	mA
I <sub>DD</sub> (PAMP)(max)	maximum power amplifier supply current in transmission mode	$V_{DD} = 5 V \pm 5\%;$ $\frac{Z_{L} = 1 \Omega}{DATA_{IN}} = LOW$	_	76	-	mA
DATA <sub>IN</sub> input	, PD input: DATA <sub>OUT</sub> outpu	t, CLK <sub>OUT</sub> output				
V <sub>IH</sub>	HIGH-level input voltage		0.2V <sub>DD</sub> + 0.9	_	V <sub>DD</sub> + 0.5	V
V <sub>IL</sub>	LOW-level input voltage		-0.5	-	$0.2V_{DD} - 0.1$	V
V <sub>OH</sub>	HIGH-level output voltage	I <sub>OH</sub> = -1.6 mA	2.4	-	-	V
V <sub>OL</sub>	LOW-level output voltage	I <sub>OL</sub> = 1.6 mA	-	-	0.45	V
•	nd OSC2 output (OSC2 on ernal clock generator)	ly used for driving ext	ernal quartz cry	vstal; mu	st be left open	when
V <sub>IH</sub>	HIGH-level input voltage		0.7V <sub>DD</sub>	-	V <sub>DD</sub> + 0.5	V
V <sub>IL</sub>	LOW-level input voltage		-0.5	_	$0.2V_{DD} - 0.1$	V
V <sub>OH</sub>	HIGH-level output voltage	I <sub>OH</sub> = -1.6 mA	2.4	-	-	V
V <sub>OL</sub>	LOW-level output voltage	I <sub>OL</sub> = 1.6 mA	-	-	0.45	V
Clock						
f <sub>osc</sub>	oscillator frequency		6.080	-	9.504	MHz
f <sub>osc</sub> f <sub>cr</sub>	ratio between oscillator and carrier frequency		-	64	-	
f <sub>osc</sub> f <sub>clkout</sub>	ratio between oscillator and clock output frequency		-	2	_	

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Transmissio	on mode	1		<b>I</b>		I
f <sub>cr</sub>	carrier frequency	f <sub>osc</sub> = 8.48 MHz	-	132.5	_	kHz
t <sub>su</sub>	set-up time of the shaped burst	f <sub>osc</sub> = 8.48 MHz; see Fig.8	-	170	-	μs
t <sub>h</sub>	hold time of the shaped burst	f <sub>osc</sub> = 8.48 MHz; see Fig.8	-	170	-	μs
t <sub>W(DI)(min)</sub>	minimum pulse width of DATA <sub>IN</sub> signal	f <sub>osc</sub> = 8.48 MHz; see Fig.8	-	190	-	μs
V <sub>o(rms)</sub>	output carrier signal (RMS value)	Z <sub>L</sub> = CISPR16 DATA <sub>IN</sub> = LOW	120	_	122	dBμV
I <sub>o(max)</sub>	power amplifier maximum output current (peak value)	$\frac{Z_{L} = 1}{DATA_{IN}} \Omega;$	_	160	-	mA
Zo	output impedance of the power amplifier		-	5	-	Ω
Vo	output DC level at TX <sub>OUT</sub>		-	2.5	-	V
THD	total harmonic distortion on CISPR16 load with the coupling network (measured on the first ten harmonics)	$\label{eq:vorms} \begin{array}{l} V_{o(rms)} = 121 \ dB\mu V \ on \\ CISPR16 \ load; \\ f_{osc} = 8.48 \ MHz; \\ \overline{DATA}_{IN} = LOW \ (no \\ modulation); \\ see \ Figs \ 3 \ and \ 16 \end{array}$	-	-55	-	dB
B <sub>-20dB</sub>	bandwidth of the shaped output signal (at –20 dB) on CISPR16 load with the coupling network	$\label{eq:Vo(rms)} \begin{array}{l} V_{o(rms)} = 121 \ dB\mu V \ on \\ CISPR16 \ load; \\ \hline f_{osc} = 8.48 \ MHz; \\ \hline DATA_{IN} = 300 \ Hz; \\ duty \ factor = 50\%; \\ see \ Fig.4 \end{array}$	-	3000	-	Hz
Reception m	node					
V <sub>i(rms)</sub>	analog input signal (RMS value)		82	-	122	dBμV
VI	DC level at pin RX <sub>IN</sub>		-	2.5	_	V
Zi	RX <sub>IN</sub> input impedance		-	50	-	kΩ
R <sub>AGC</sub>	automatic gain control range		-	36	-	dB
t <sub>c(AGC)</sub>	automatic gain control time constant	f <sub>osc</sub> = 8.48 MHz; see Fig.5	-	296	-	μs
t <sub>d(dem)(su)</sub>	demodulation delay set-up time	f <sub>osc</sub> = 8.48 MHz; see Fig.15	-	350	400	μs

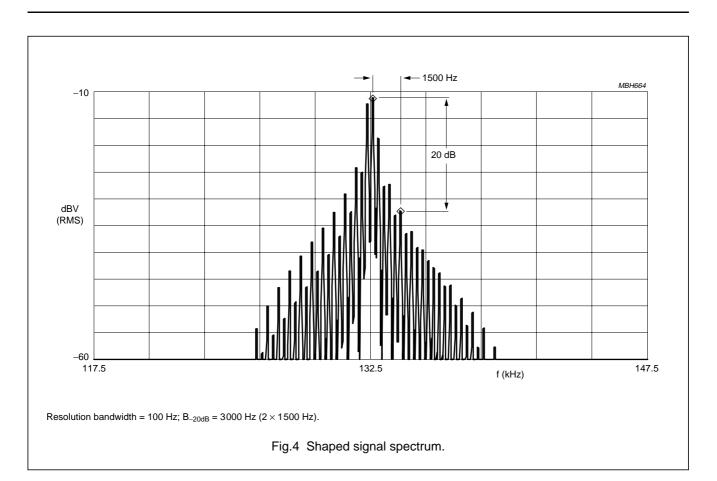
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t <sub>d(dem)(h)</sub>	demodulation delay hold time	f <sub>osc</sub> = 8.48 MHz; see Fig.15	-	420	470	μs
B <sub>det</sub>	detection bandwidth	f <sub>osc</sub> = 8.48 MHz	-	3	-	kHz
BER	bit error rate	f <sub>osc</sub> = 8.48 MHz; 600 baud; S/N = 35 dB; signal 76 dBμV; see Fig.17	-	1	-	1 × 10 <sup>-4</sup>
Power-up tin	ning					·
t <sub>d(pu)(TX)</sub>	delay between power-up and DATA <sub>IN</sub> in transmission mode	$\begin{array}{l} {\sf XTAL} = 8.48 \; {\sf MHz}; \\ {\sf C1} = {\sf C2} = 27 \; {\sf pF}; \\ {\sf R}_{\sf p} = 2.2 \; {\sf M}\Omega; \\ {\sf see \; Fig.10} \end{array}$	-	1		μs
t <sub>d(pu)(RX)</sub>	delay between power-up and DATA <sub>OUT</sub> in reception mode	$\begin{array}{l} {\sf XTAL} = 8.48 \; {\sf MHz}; \\ {\sf C1} = {\sf C2} = 27 {\sf pF}; \\ {\sf R}_{\sf p} = 2.2 \; {\sf M}\Omega; \\ {\sf f}_{\sf RXIN} = 132.5 \; {\sf kHz}; \\ {\sf 120} \; {\sf dB} {\sf \muV} \; {\sf sinewave}; \\ {\sf see} \; {\sf Fig.11} \end{array}$	-	1	-	μs
Power-dowr	n timing		·			
t <sub>d(pd)(TX)</sub>	$\frac{\text{delay between PD} = 0 \text{ and}}{\text{DATA}_{\text{IN}} \text{ in transmission}}$	f <sub>osc</sub> = 8.48 MHz; see Fig.12	-	10	-	μs
t <sub>d(pd)(RX)</sub>	$\frac{\text{delay between PD} = 0 \text{ and}}{\text{DATA}_{\text{OUT}} \text{ in reception}}$ mode	$\label{eq:fosc} \begin{array}{l} f_{osc} = 8.48 \mbox{ MHz}; \\ f_{RXIN} = 132.5 \mbox{ kHz}; \\ 120 \mbox{ dB}\mu V \mbox{ sinewave}; \\ see \mbox{ Fig.13} \end{array}$	-	500	-	μs
t <sub>active(min)</sub>	minimum active time with T = 10 ms power-down period in reception mode	$\label{eq:fosc} \begin{array}{l} f_{osc} = 8.48 \mbox{ MHz;} \\ f_{RXIN} = 132.5 \mbox{ kHz;} \\ 120 \mbox{ dB}\mu V \mbox{ sinewave;} \\ see \mbox{ Fig.14} \end{array}$	-	1	_	μs

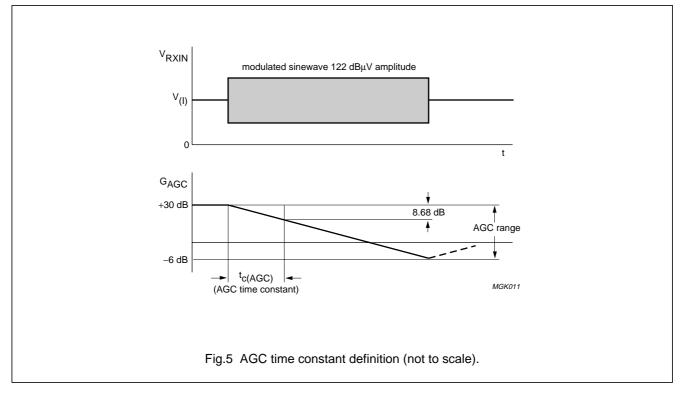
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Fig.3 Carrier spectrum.

TDA5051A

# Home automation modem

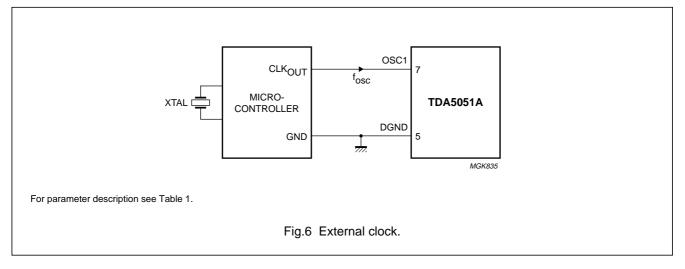


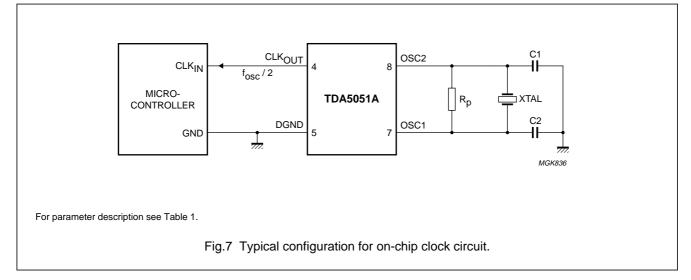


# TDA5051A

### TIMING

### **Configurations for clock**



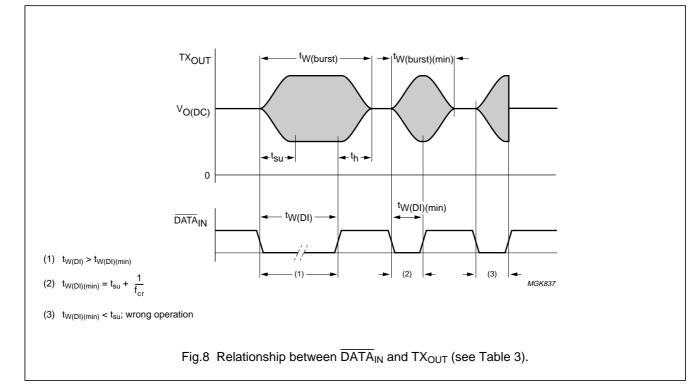


### Table 1 Clock oscillator parameters

f <sub>osc</sub>	f <sub>cr</sub>	<sup>1/2</sup> f <sub>osc</sub>	EXTERNAL COMPONENTS
OSCILLATOR	CARRIER	CLOCK OUTPUT	
FREQUENCY	FREQUENCY	FREQUENCY	
6.080 to 9.504 MHz	95 to 148.5 kHz	3.040 to 4.752 MHz	$\begin{array}{l} \text{C1}=\text{C2}=\text{27 to 47 pF};\\ \text{R}_{\text{p}}=\text{2.2 to 4.7 M}\Omega;\\ \text{XTAL}=\text{standard quartz crystal} \end{array}$

SYMBOL	PARAMETER	CONDITIONS	UNIT
f <sub>osc</sub>	oscillator frequency	with on-chip oscillator: frequency of the crystal quartz; with external clock: frequency of the signal applied at OSC1	Hz
f <sub>CLKOUT</sub>	clock output frequency	<sup>1</sup> / <sub>2</sub> f <sub>osc</sub>	Hz
f <sub>cr</sub>	carrier frequency/digital filter tuning frequency	<sup>1</sup> / <sub>64</sub> f <sub>osc</sub>	Hz
t <sub>su</sub>	set-up time of the shaped burst	$\frac{23}{f_{cr}}$ or $\frac{1472}{f_{osc}}$	S
t <sub>h</sub>	hold time of the shaped burst	$\frac{23}{f_{cr}} \text{ or } \frac{1472}{f_{osc}}$	S
t <sub>W(DI)(min)</sub>	minimum pulse width of DATA <sub>IN</sub> signal	$t_{su} + \frac{1}{f_{cr}}$	S
t <sub>W(burst)(min)</sub>	minimum burst time of V <sub>O(DC)</sub> signal	t <sub>W(DI)(min)</sub> + t <sub>h</sub>	S
t <sub>c(AGC)</sub>	AGC time constant	2514 f <sub>osc</sub>	S
t <sub>su(demod)</sub>	demodulation set-up time	3200 f <sub>osc</sub> (≈max.)	S
t <sub>h(demod)</sub>	demodulation hold time	3800 <sub>fosc</sub> (≈max.)	S

Table 2 Calculation of parameters depending on the clock frequency



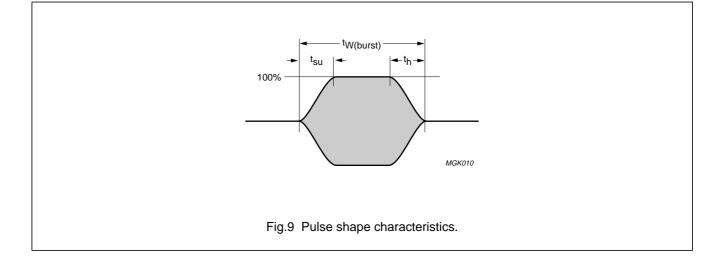
# TDA5051A

 $\textbf{Table 3} \quad \text{Relationship between } \overline{\text{DATA}}_{\text{IN}} \text{ and } \text{TX}_{\text{OUT}}$ 

PD	DATA <sub>IN</sub>	TX <sub>OUT</sub>
1	X <sup>(1)</sup>	high impedance
0	1	high impedance (after t <sub>h</sub> )
0	0	active with DC offset

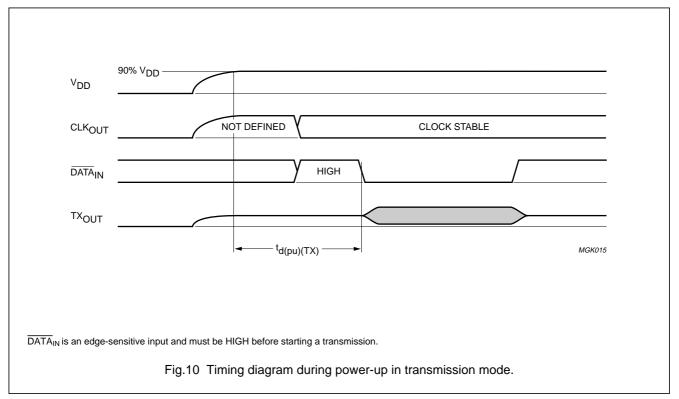
### Note

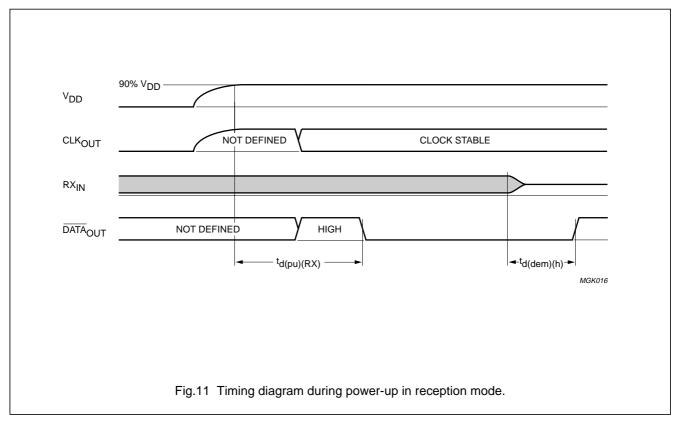
1. X = don't care



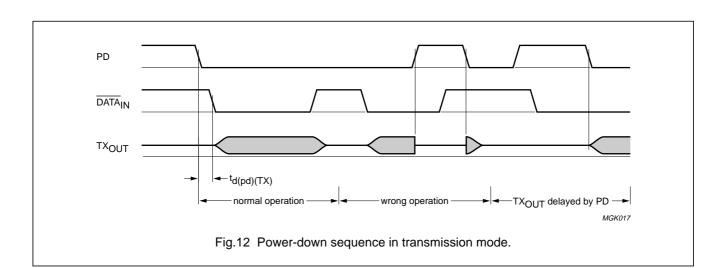
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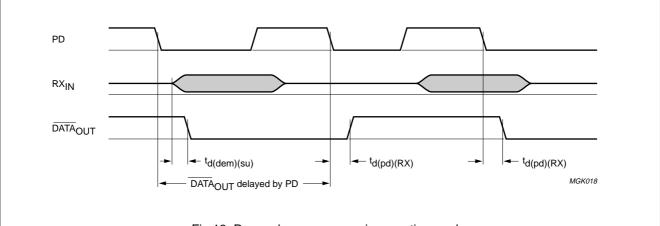
### **Timing diagrams**



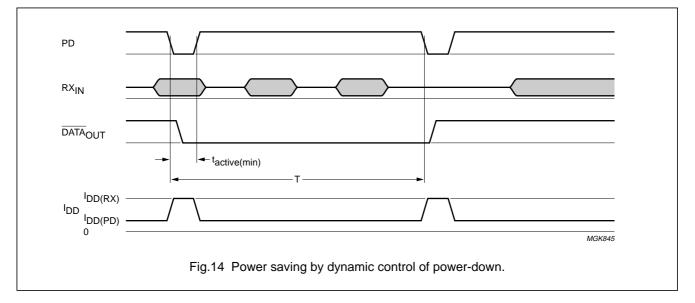


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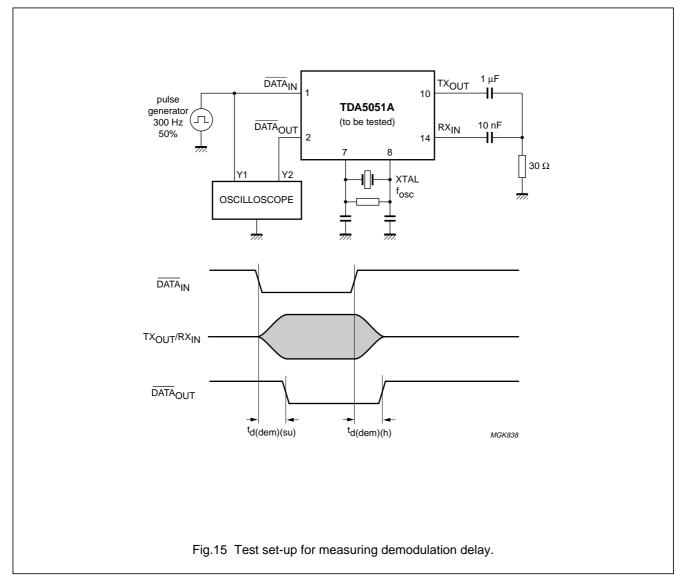


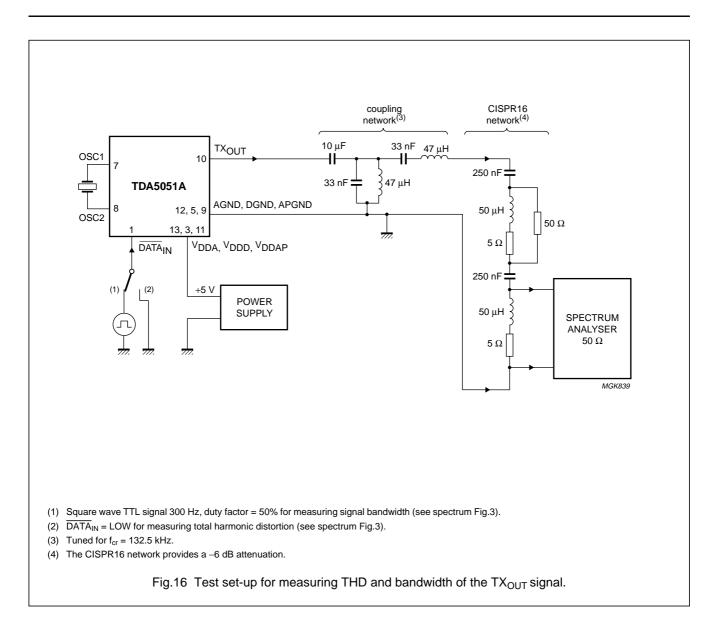
### Fig.13 Power-down sequence in reception mode.

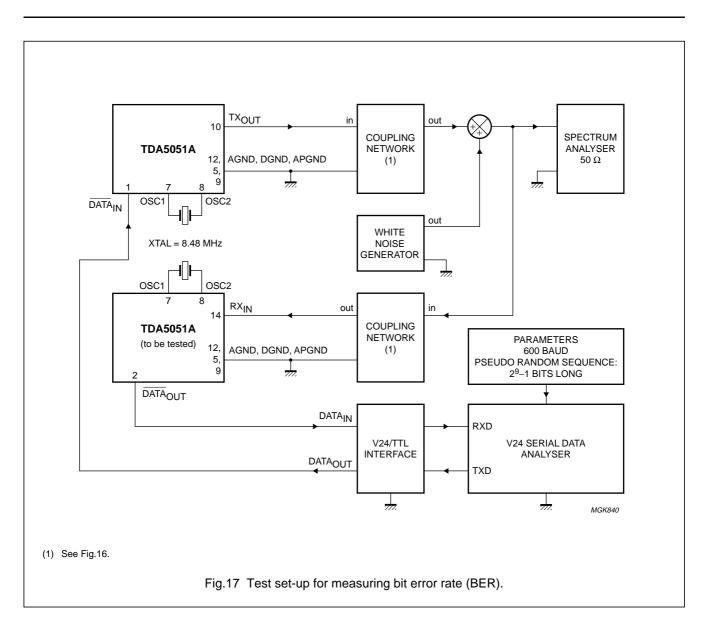


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### **TEST INFORMATION**

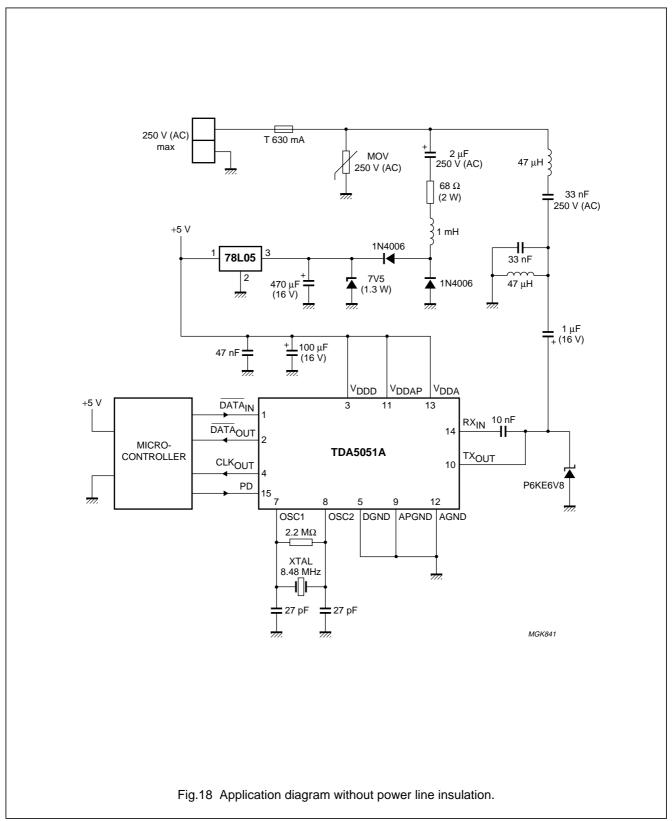


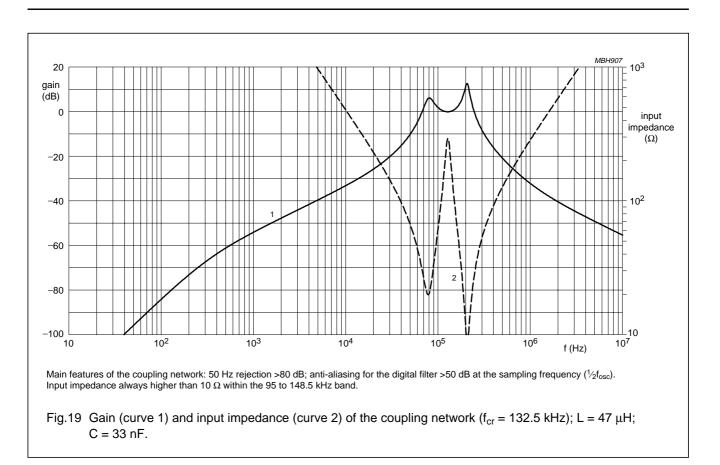


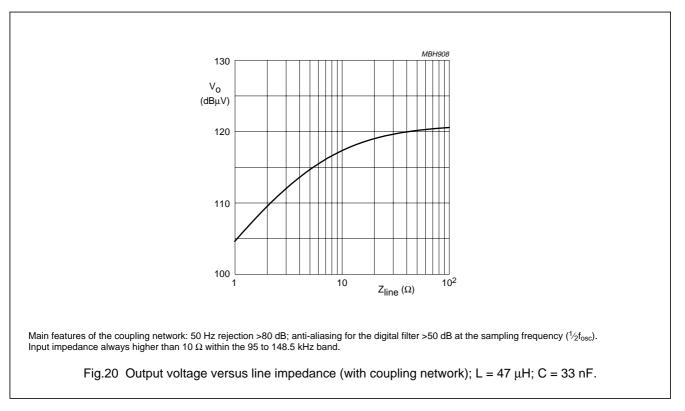


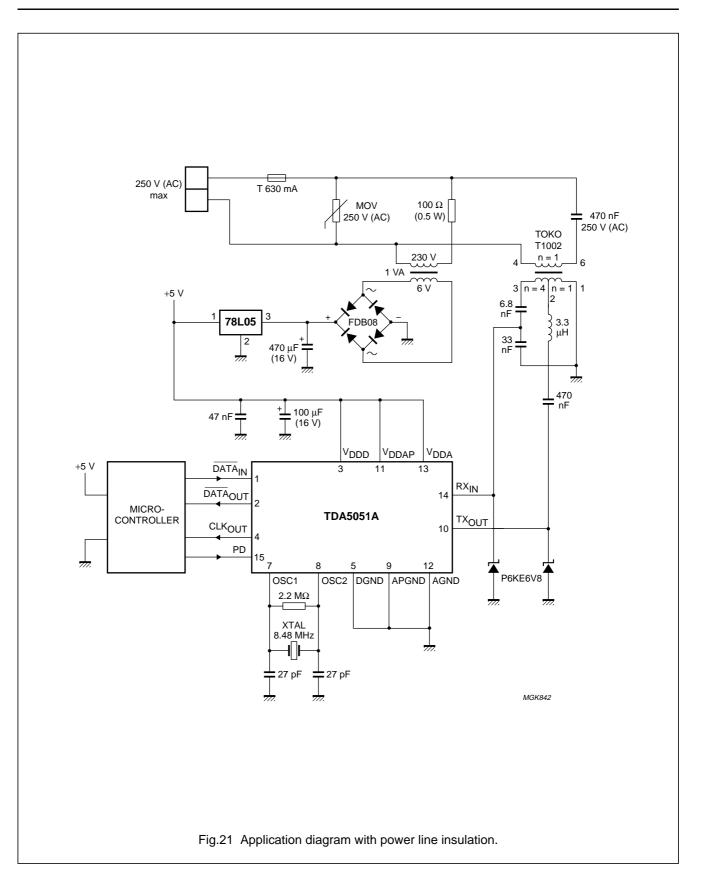
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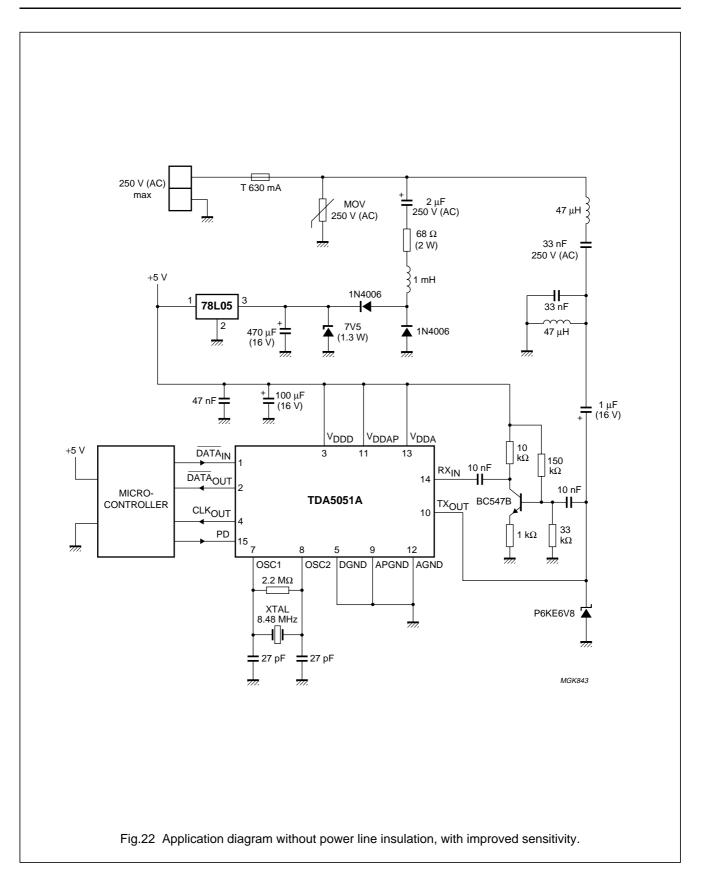
### **APPLICATION INFORMATION**

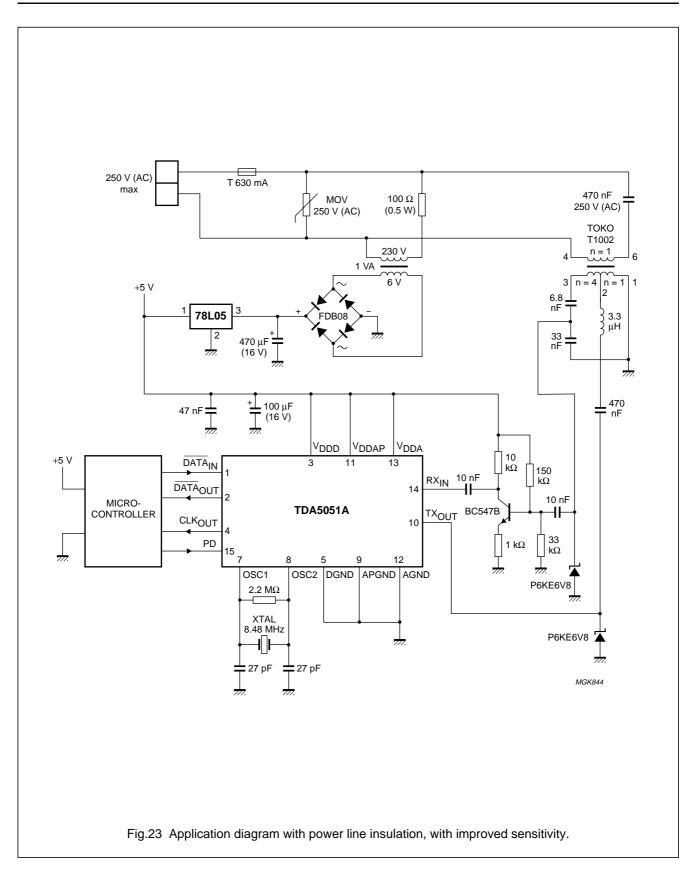












# TDA5051A

### PACKAGE OUTLINE

### SO16: plastic small outline package; 16 leads; body width 7.5 mm SOT162-1 D Α Х = v (M) A $H_{E}$ 🛛 у 16 Q pin 1 index Lp - 1 Π Π Г 8 detail X ► e + **(** w M bp 10 mm 5 0 scale DIMENSIONS (inch dimensions are derived from the original mm dimensions) Α z<sup>(1)</sup> D<sup>(1)</sup> E<sup>(1)</sup> UNIT ${\sf H}_{\sf E}$ **A**<sub>1</sub> L Q θ С v w A<sub>2</sub> $A_3$ bp е Lp у max 0.30 2.45 0.49 0.32 10.5 7.6 10.65 1.1 1.1 0.9 2.65 mm 0.25 1.27 1.4 0.25 0.25 0.1 0.10 2.25 0.36 0.23 7.4 10.00 0.4 1.0 0.4 10.1 8° 0° 0.035 0.012 0.419 0.043 0.043 0.096 0.019 0.013 0.41 0.30 inches 0.10 0.004 0.01 0.050 0.055 0.01 0.01 0.004 0.089 0.014 0.009 0.40 0.29 0.394 0.016 0.039 0.016 Note 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included. REFERENCES EUROPEAN OUTLINE ISSUE DATE PROJECTION VERSION IEC JEDEC EIAJ <del>95-01-24</del> 97-05-22 SOT162-1 075E03 MS-013AA

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### SOLDERING

### Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"IC Package Databook"* (order code 9398 652 90011).

### **Reflow soldering**

Reflow soldering techniques are suitable for all SO packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

### Wave soldering

Wave soldering techniques can be used for all SO packages if the following conditions are observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used
- The longitudinal axis of the package footprint must be parallel to the solder flow
- The package footprint must incorporate solder thieves at the downstream end.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

### **Repairing soldered joints**

Fix the component by first soldering two diagonallyopposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

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### DEFINITIONS

Data sheet status			
Objective specification	This data sheet contains target or goal specifications for product development.		
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.		
Product specification This data sheet contains final product specifications.			
Limiting values			
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.			
Application information			

Where application information is given, it is advisory and does not form part of the specification.

### LIFE SUPPORT APPLICATIONS

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Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB, Argentina: see South America Tel. +31 40 27 82785, Fax. +31 40 27 88399 Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113, New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND, Tel. +61 2 9805 4455, Fax. +61 2 9805 4466 Tel. +64 9 849 4160, Fax. +64 9 849 7811 Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 160 1010, Norway: Box 1, Manglerud 0612, OSLO, Fax. +43 160 101 1210 Tel. +47 22 74 8000, Fax. +47 22 74 8341 Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6, 220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773 Philippines: Philips Semiconductors Philippines Inc., 106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Belgium: see The Netherlands Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474 Brazil: see South America Poland: UI. Lukiska 10, PL 04-123 WARSZAWA, Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor, Tel. +48 22 612 2831, Fax. +48 22 612 2327 51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 689 211, Fax. +359 2 689 102 Portugal: see Spain Romania: see Italy Canada: PHILIPS SEMICONDUCTORS/COMPONENTS, Tel. +1 800 234 7381 Russia: Philips Russia, UI. Usatcheva 35A, 119048 MOSCOW, Tel. +7 095 755 6918, Fax. +7 095 755 6919 China/Hong Kong: 501 Hong Kong Industrial Technology Centre, 72 Tat Chee Avenue, Kowloon Tong, HONG KONG, Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231, Tel. +852 2319 7888, Fax. +852 2319 7700 Tel. +65 350 2538, Fax. +65 251 6500 Slovakia: see Austria Colombia: see South America Czech Republic: see Austria Slovenia: see Italy Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S, South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale, Tel. +45 32 88 2636, Fax. +45 31 57 0044 2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000, Tel. +27 11 470 5911, Fax. +27 11 470 5494 Finland: Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615800, Fax. +358 9 61580920 South America: Rua do Rocio 220, 5th floor, Suite 51, 04552-903 São Paulo, SÃO PAULO - SP, Brazil, France: 4 Rue du Port-aux-Vins. BP317. 92156 SURESNES Cedex. Tel. +55 11 821 2333, Fax. +55 11 829 1849 Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427 Spain: Balmes 22 08007 BARCELONA Germany: Hammerbrookstraße 69, D-20097 HAMBURG, Tel. +34 3 301 6312, Fax. +34 3 301 4107 Tel. +49 40 23 53 60, Fax. +49 40 23 536 300 Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM, Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS, Tel. +46 8 632 2000, Fax. +46 8 632 2745 Tel. +30 1 4894 339/239, Fax. +30 1 4814 240 Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH, Hungary: see Austria Tel. +41 1 488 2686, Fax. +41 1 481 7730 India: Philips INDIA Ltd, Band Box Building, 2nd floor, Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1, 254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025, TAIPEI, Taiwan Tel. +886 2 2134 2865, Fax. +886 2 2134 2874 Tel. +91 22 493 8541, Fax. +91 22 493 0966 Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd. Indonesia: see Singapore 209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260, Ireland: Newstead, Clonskeagh, DUBLIN 14, Tel. +66 2 745 4090, Fax. +66 2 398 0793 Tel. +353 1 7640 000, Fax. +353 1 7640 200 Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL, Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, Tel. +90 212 279 2770, Fax. +90 212 282 6707 TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007 Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7, Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3, 252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461 20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557 United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Haves. Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108, MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421 Tel. +81 3 3740 5130, Fax. +81 3 3740 5077 United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409, Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL, Tel. +1 800 234 7381 Tel. +82 2 709 1412, Fax. +82 2 709 1415 Uruguay: see South America Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR, Vietnam: see Singapore Tel. +60 3 750 5214, Fax. +60 3 757 4880 Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD, Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905, Tel. +381 11 625 344, Fax.+381 11 635 777 Tel. +9-5 800 234 7381

For all other countries apply to: Philips Semiconductors, Marketing & Sales Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

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